

ECE ECE145C (undergrad) and ECE218c (graduate)

Mid-Term Exam. Nov 5, 2007

Do not open exam until instructed to.

Open book

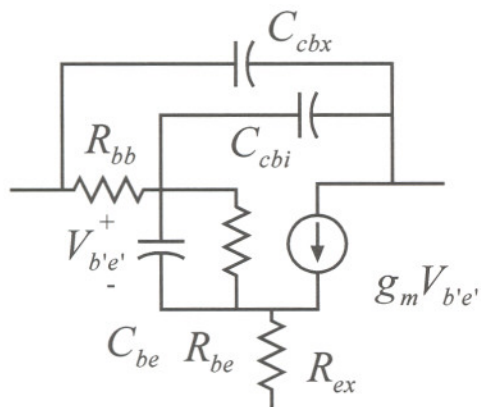
Use any and all reasonable approximations (5% accuracy is fine.) , ***AFTER STATING THEM.***

Problem	Points Received	Points Possible
1a		10
1b		5
1c		20
1d		5
1e		10
1f		10
2a		10
2b		10
2c		10

Name: Solati

Problem 1, 70 points

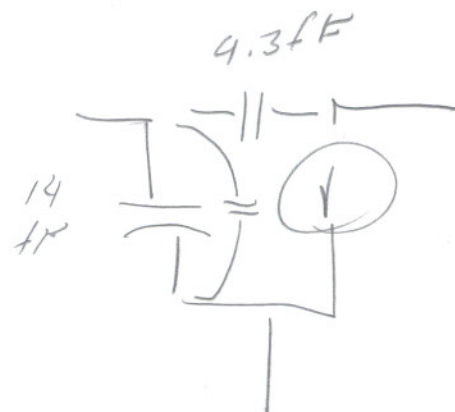
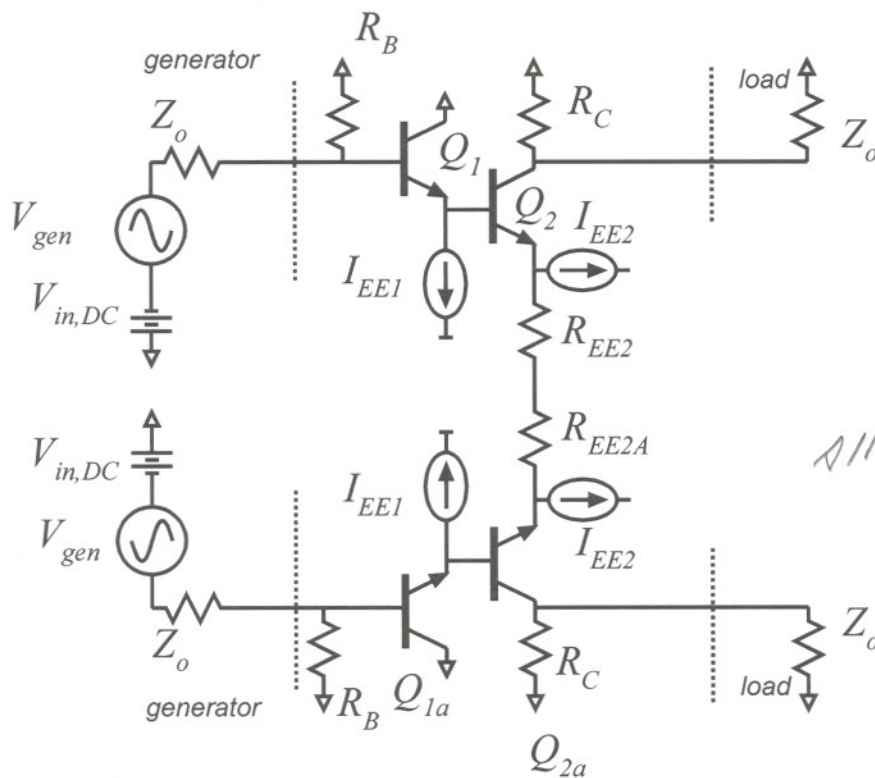
You will be using the device model below:



$C_{be} = C_{be,depl} + g_m \tau_f$. $C_{je} = 14 \text{ fF}$,
 $\beta = \infty$, $C_{cbi} = 4.3 \text{ fF}$, $C_{cbx} = 0 \text{ fF}$, $R_{bb} = 0$
 Ohms, $R_{ex} = 0$ Ohms, and $\tau_f = 0.44 \text{ ps}$. This
 transistor model has 5 um^2 emitter area.

The transistors have a $V_{be} = 0.9 \text{ Volts}$ when
 operating at 2.0 mA/um^2 .

You will be working with the circuit below

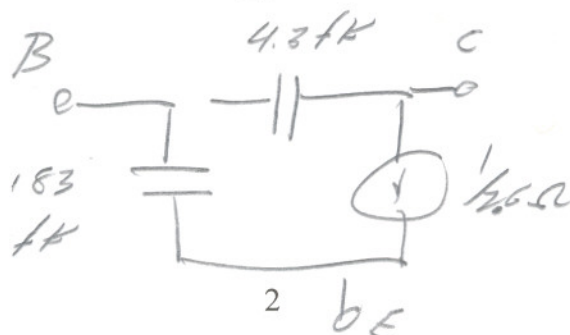


C_{dH}

$$\text{All } I_E = I_C = 10 \mu A$$

$$g_m = 1/2.6 \Omega$$

$$C_{dH} = g_m \tau_f = 169 \text{ fF}$$



$$C_{be} = g_m \tau_f + C_{dH} = 183 \text{ fF}$$

Part a: 10 points:

S-parameter design, gain definitions

Think carefully before answering---this is mostly a matter of getting details correct.

For differential input signals, the amplifier half-circuit is to have 50 Ohms input and 50 Ohms output impedance. Z_o is to be 50 Ohms.

The amplifier is to be designed for $S_{21}=10$ dB at mid-band frequencies

All transistors are biased at 10 mA current

($V_{in,DC}$ is to be selected so that the amplifier input and output DC levels are identical---we will use this fact in part b)

Find the following:

$$R_C = \underline{50\Omega} \quad R_B = \underline{50\Omega}$$

$$R_{EE2} = \underline{5.3\Omega}$$

$$A_v = A_{v1} A_{v2} = 3.16 = 1 \cdot A_{v2}$$

$$\Rightarrow A_{v2} = 3.16 = \frac{25\Omega}{R_{EE} + 2.6\Omega} \Rightarrow R_{EE} + 2.6 = \frac{25\Omega}{3.16} = 7.91\Omega$$

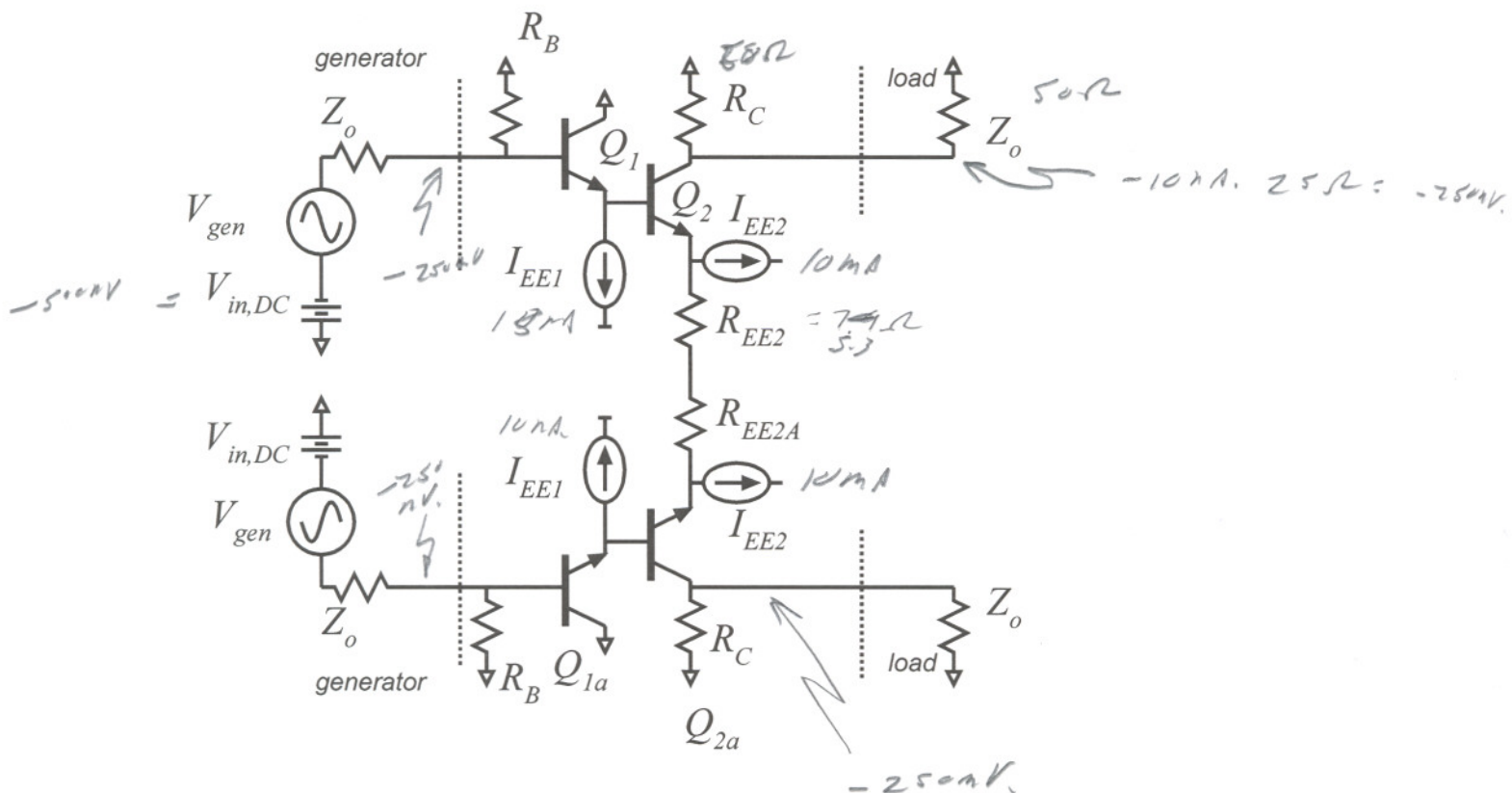
$$\Rightarrow R_{EE} = \underline{\underline{5.3\Omega}}$$

Part b, 5 points

DC bias

$V_{in,DC}$ is to be selected so that the amplifier input and output DC levels are identical (this represents the condition of a cascade of similar amplifiers)

Draw the DC node voltages on the circuit diagram



bandwidth calculations

Using the method of time constants, find the coefficients a_1 and a_2 of the transfer function. **We will simplify the problem by NOW SETTING C_{cb1} to ZERO.**

The remaining capacitors are labeled $C_1=C_{be1}$, $C_2=C_{cb2}$, $C_3=C_{be2}$

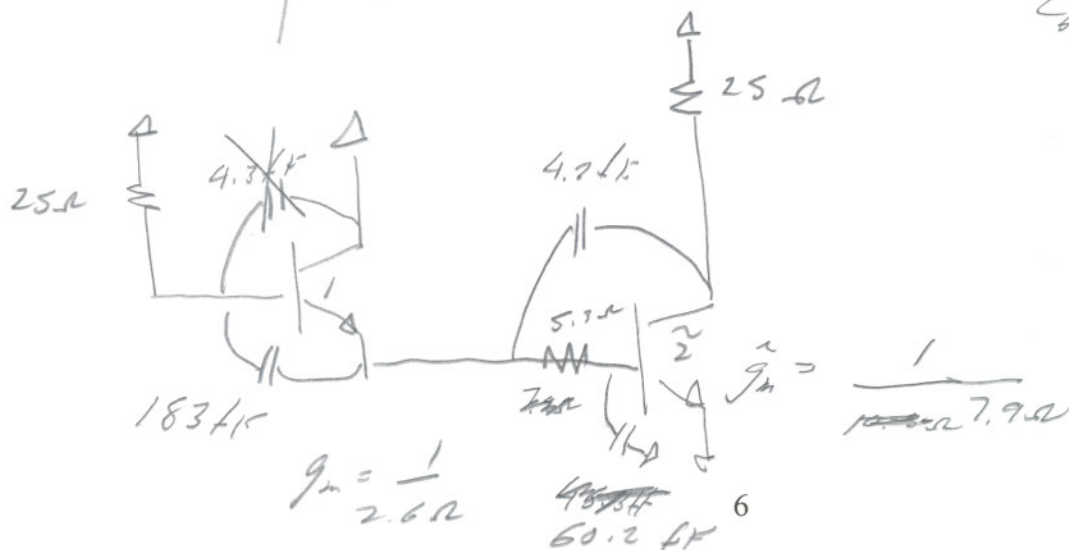
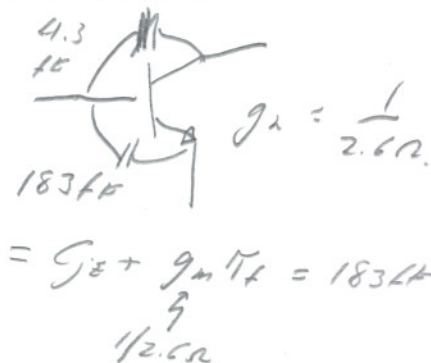
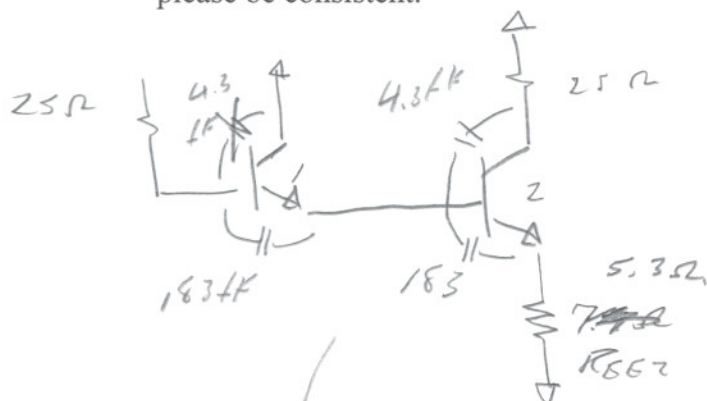
$$R_{11}^0 = 2.6 \Omega \quad R_{22}^0 = 35.8 \Omega$$

$$R_{33}^0 = 7.952 \quad R_{22}^1 = 129.2$$

$$R_{33}^1 = 30.3 \Omega \quad R_{33}^2 = 7.3 \Omega$$

$$a_1 = 1.11 \text{ ps}, \quad a_2 = 1.34 (10^{-24}) \text{ sec}^2$$

You may use the degeneration approximation if you wish, but please make this clear and please be consistent.

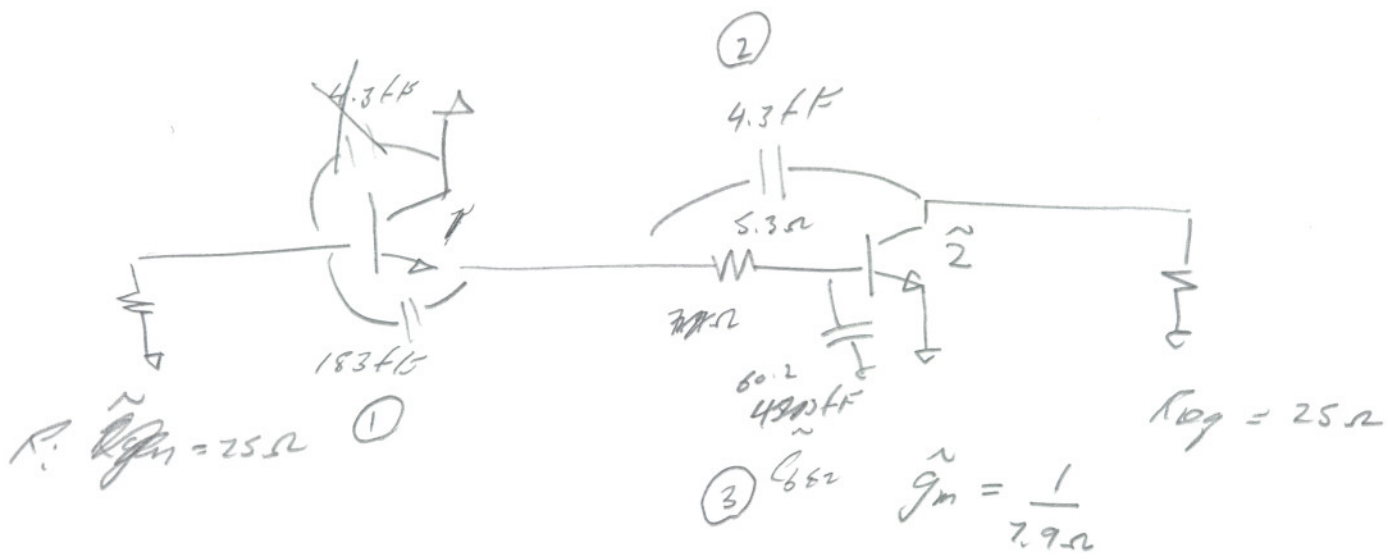


$$C_{\text{eq}} = C_{\text{eq}} \cdot \frac{2.6 \mu\text{F}}{2.6 \mu\text{F} + 5.3 \mu\text{F}}$$

$$= 45 \mu\text{F}$$

$$= 60.2 \mu\text{F}$$

$$\frac{1}{10.5 \Omega} = 7.9 \Omega$$



$$R_{11}^0 = 1/g_{m1} = 2.6 \Omega$$

$$R_{11}^0 C_1 = 2.6 \Omega \cdot 183 \text{ fF} = 476 \text{ fS}$$

$$R_{22}^0 = (1/g_{m1}) (1 + g_{m2} R_{eq}) + R_{eq}$$

$$= 2.6 \Omega \left(1 + \frac{25 \Omega}{7.9 \Omega} \right) + 25 \Omega = 2.6 (1 + 3.16) + 25 \Omega$$

$$R_{22}^0 = \underline{35.8 \Omega}$$

$$R_{22}^0 C_2 = 35.8 \Omega \cdot 4.3 \text{ fF} = \underline{154 \text{ fS}}$$

$$R_{33}^0 = 1/g_{m1} + 5.3 \Omega = 2.6 \Omega + 5.3 \Omega = 7.9 \Omega$$

$$R_{33}^0 C_3 = 7.9 \Omega \cdot 60.2 \text{ fF} = \underline{476 \text{ fS}}$$

$$\tau_1 = 476 + 476 + 154 \text{ fS} = 1.11 \text{ ps}$$

$$R_{22}^1 = 25 \Omega (1 + 3.16) + 25 \Omega = 25 \Omega (5.16) = 129 \Omega$$

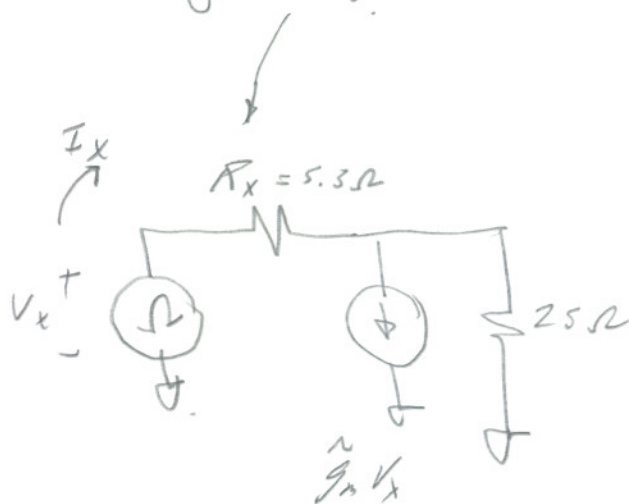
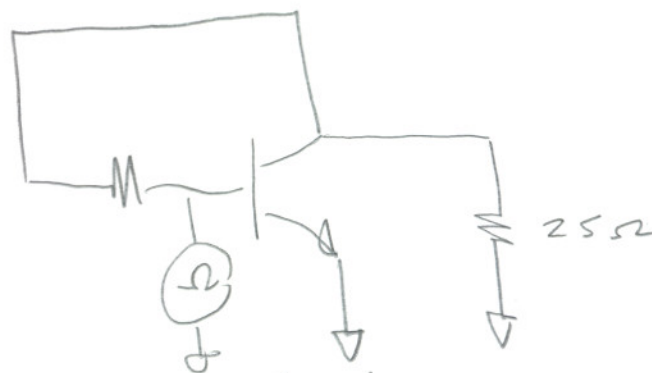
$$C_1 R_{11}^0 R_{22}^1 C_2 = 476 \text{ fS} (129 \Omega) (4.3 \text{ fF}) = 2.64 \cdot 10^{-25} \text{ sec}^2$$

$$R_{33}^1 = 25 \Omega + 5.3 \Omega = 30.3 \Omega$$

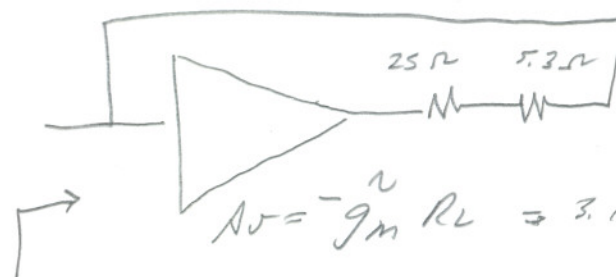
$$C_1 R_{11}^0 R_{33}^1 C_3 = (476 \text{ fS}) 30.3 \Omega \cdot 60.2 \text{ fF} = 8.7 \cdot 10^{-25} \text{ sec}^2$$

R

$$R_{33}^2 = 7.3 \Omega$$



$$\tilde{g}_m = \frac{1}{7.9 \Omega}$$



$$A_v = -\tilde{g}_m R_L \approx 3.16$$

$$R = \frac{25 \Omega + 5.3 \Omega}{4.16} = \underline{\underline{7.28 \Omega}}$$

$$C_2 R_{22}^0 R_{33}^2 C_3 = (476 \text{ pF})(7.3 \Omega) \cdot 60.2 \text{ pF}$$

$$= 2.01 \cdot 10^{-25} \text{ sec}^2$$

$$a_2 = \text{sum of 3 terms above} = 1.34 \cdot 10^{-24} \text{ sec}^2$$

part D, 5 points
finding the poles

If the poles are widely separated, find the frequency of the lower pole by the separated pole approximation.

If the poles are complex, find the damped resonant frequency f_d and the damping factor ζ .

$$a_1 = 1.11 \cdot 10^{-12} \text{ sec}$$

$$a_2 = 1.34 (10^{-24}) \text{ sec}^2$$

try SPA : $\frac{a_2}{a_1} = 1.21 \cdot 10^{-12} \text{ sec}^2 \approx a_1 \Rightarrow \underline{\underline{\text{SPA fails}}}$

try complex roots

$$1 + a_1 s + a_2 s^2 = 1 + \frac{2\zeta}{\omega_n} s + \frac{s^2}{\omega_n^2}$$

$$\omega_n = \frac{1}{\sqrt{a_2}} = 8.64 \cdot 10^{11} \text{ rad/sec} \Rightarrow f_n = 137.4 \text{ GHz}$$

$$a_1 = 2\zeta/\omega_n \Rightarrow \zeta = \frac{a_1 \omega_n}{2} = \frac{a_1}{2\sqrt{a_2}} = \underline{\underline{0.48}}$$

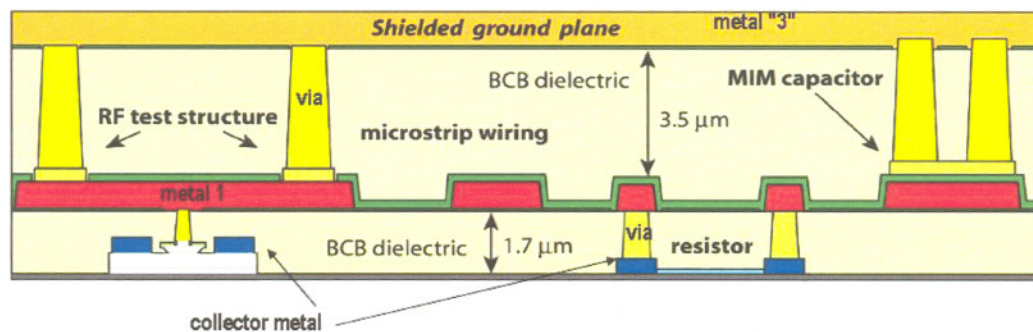
$\zeta \approx 0.5$	$f_n \approx 137 \text{ GHz}$
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Part E, 10 points

mask layout and transmission-line issues.

Resistors in the process have 50 Ohm sheet resistance and carry a maximum of 2 mA current per micron of width. Transmission lines are inverted microstrip, and have a characteristic impedance of $Z_o \sim 377\Omega * \epsilon_r^{-1/2} * H / (H + W)$, where W is the conductor width, $H = 5$ micrometers and $\epsilon_r = 3$. Their propagation velocity is $v \sim c * \epsilon_r^{-1/2}$, where c is the speed of light. Wires also carry maximum of 2 mA current per micron of width

The process cross section is like so:



Using notation like so, *carefully* draw a mask layout of the IC. Give lengths and widths of all your resistors and all your wires. Make sure that your layout includes the outline of the ground plane and shows the input and output connections. Indicate the current sources by resistors of large but unspecified length and of a width consistent with the current density limits given above.

interconnect
(label with layer #)



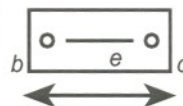
resistor with
collector metal
contacts



via

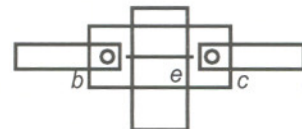


transistor



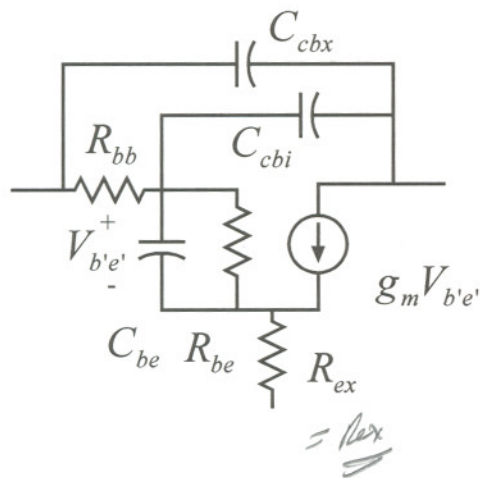
emitter length + about 5 μm

transistor
with connections



Problem 2, 30 points

You will be using the device model below:

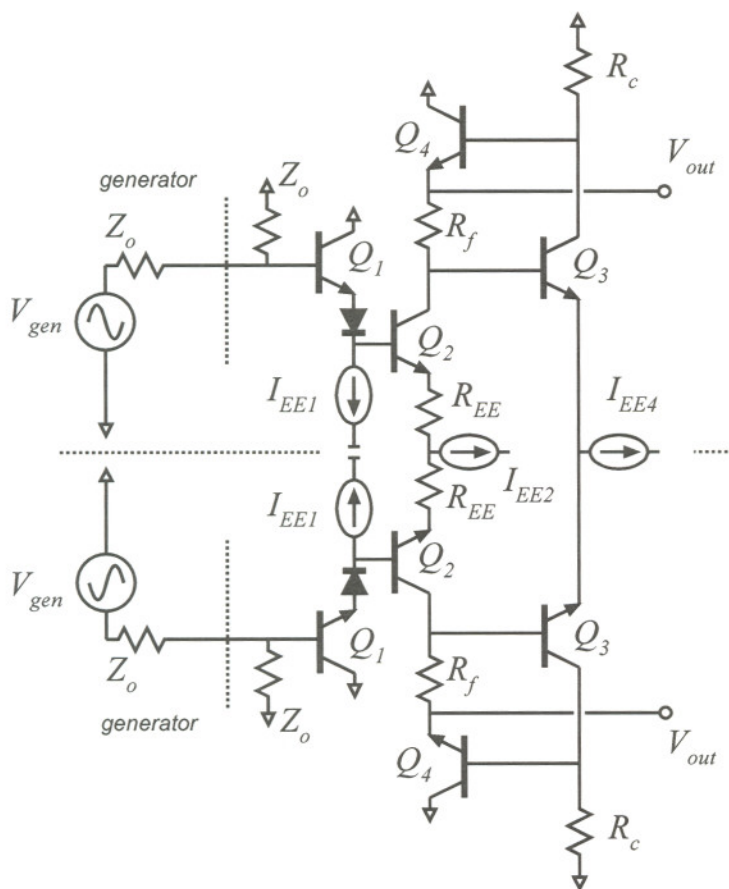


$C_{be} = C_{be,depl} + g_m \tau_f$. **Cje=6 fF**, $\beta = \infty$, **Ccbi=3 fF**, $C_{cbx}=0$ fF, **Rbb=15 Ohms**, $R_{ex}=0$ Ohms, and **$\tau_f=0.25$ ps**. This transistor model has **1 μm^2** emitter area.

The transistors have a $V_{be}=0.9$ Volts when operating at **10.0 mA/ μm^2** .

(these #s for 250 nm generation InP HBT--except the HBT really has 5-10 Ohm- μm^2 emitter resistivity)

You will be working with the circuit below--the dotted line indicates virtual ground for the differential half-circuit. This is a standard Cherry-Hooper drawn floorplan-style.



Part a: 10 points:

DC bias

$$\frac{kT}{q} \ln \frac{2 \text{ mA}}{10 \text{ nA}} = 42 \text{ mV}, \text{ so } V_{be} = 0.7 \text{ V} - 42 \text{ mV} = 0.658 \text{ V} \approx 0.9 \text{ V}$$

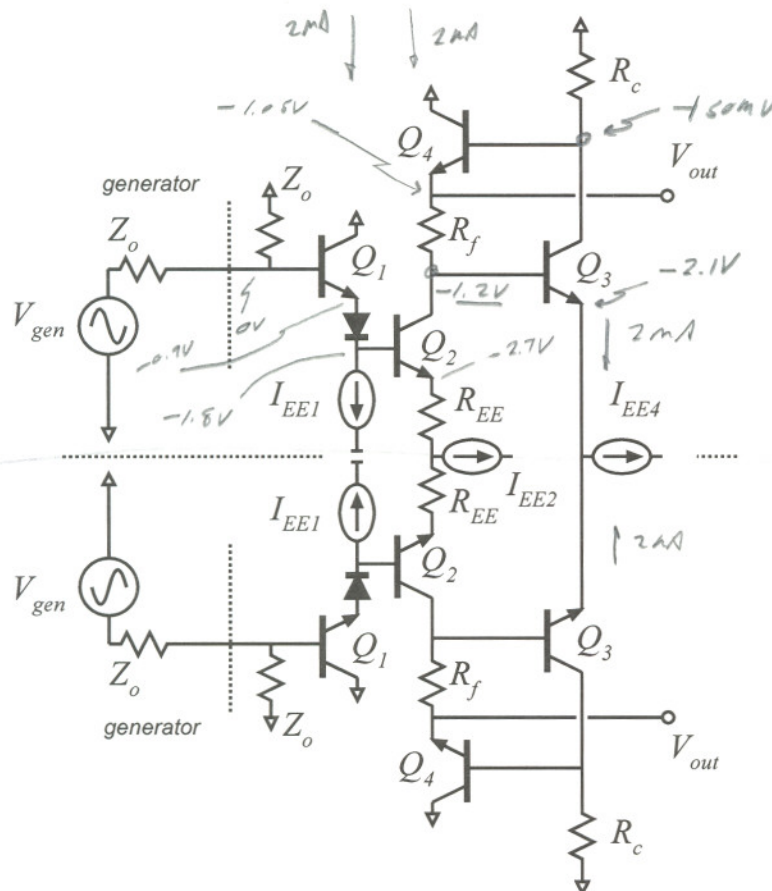
All transistors are biased at 2 mA emitter or collector current. Z_o is 50 Ohms. The voltage drops across R_f and R_c are both 150 mV. The DC input voltage is Zero volts.

Find the following:

$$R_C = 75 \Omega \quad R_F = 75 \Omega$$

$$I_{EE1} = 2 \text{ mA} \quad I_{EE2} = 4 \text{ mA} \quad I_{EE3} = 4 \text{ mA}$$

Draw all node voltages and branch currents on the circuit diagram.



$$R_C = \frac{150 \text{ mV}}{2 \text{ mA}} = 75 \Omega = R_C$$

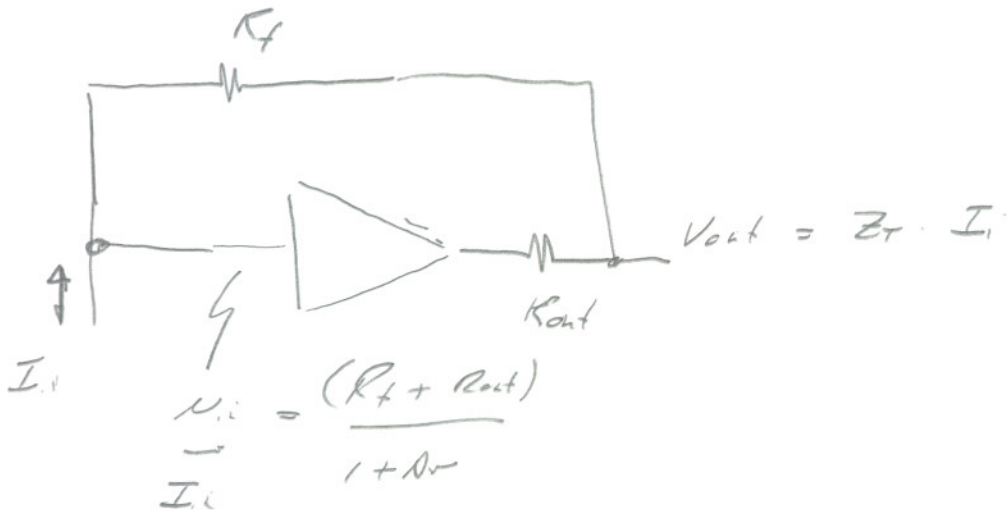
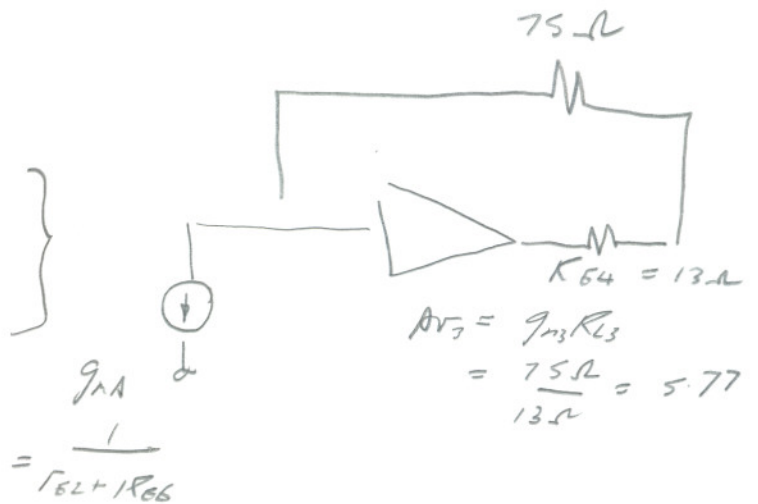
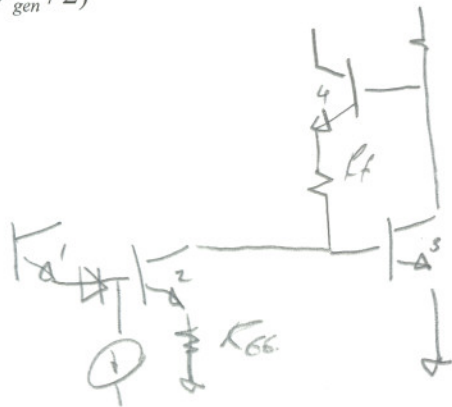
Part b, 10 points

Circuit gains

$$r_E = 13 \Omega$$

Find the value of R_{EE} required for 10 dB circuit gain---gain being defined as

$$V_{out} / (V_{gen} / 2)$$



$$V_{out} - V_{i,i} = -R_f I_{i,i}$$

$$Z_T = R_f - \frac{R_f + R_{out}}{1 + A_v}$$

$$= 75 \Omega - \frac{75 \Omega + 13 \Omega}{6.77} = 75 \Omega - 12.99 \Omega$$

$$= \underline{\underline{62 \Omega}}$$

$$A_v = 3.16 = \frac{62 \Omega}{r_{E2} + R_{EE}}$$

$$\rightarrow r_{E2} + R_{EE} = 19.6 \Omega$$

$$R_{EE} = 19.6 - r_{E2} = 19.6 - 13 \Omega$$

$$= \underline{\underline{6.62 \Omega}}$$

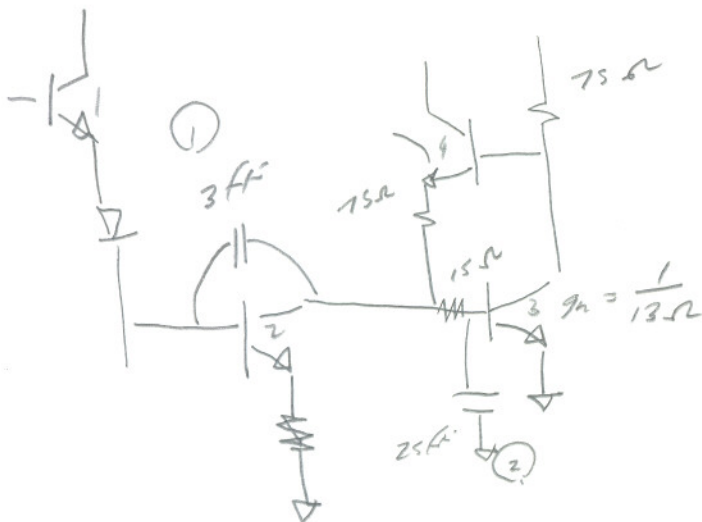
Part C, 10 points
bandwidth calculations

considering only the base-emitter capacitance of Q3 and the base-collector capacitance of Q2, determine the circuit first and second-order time constants

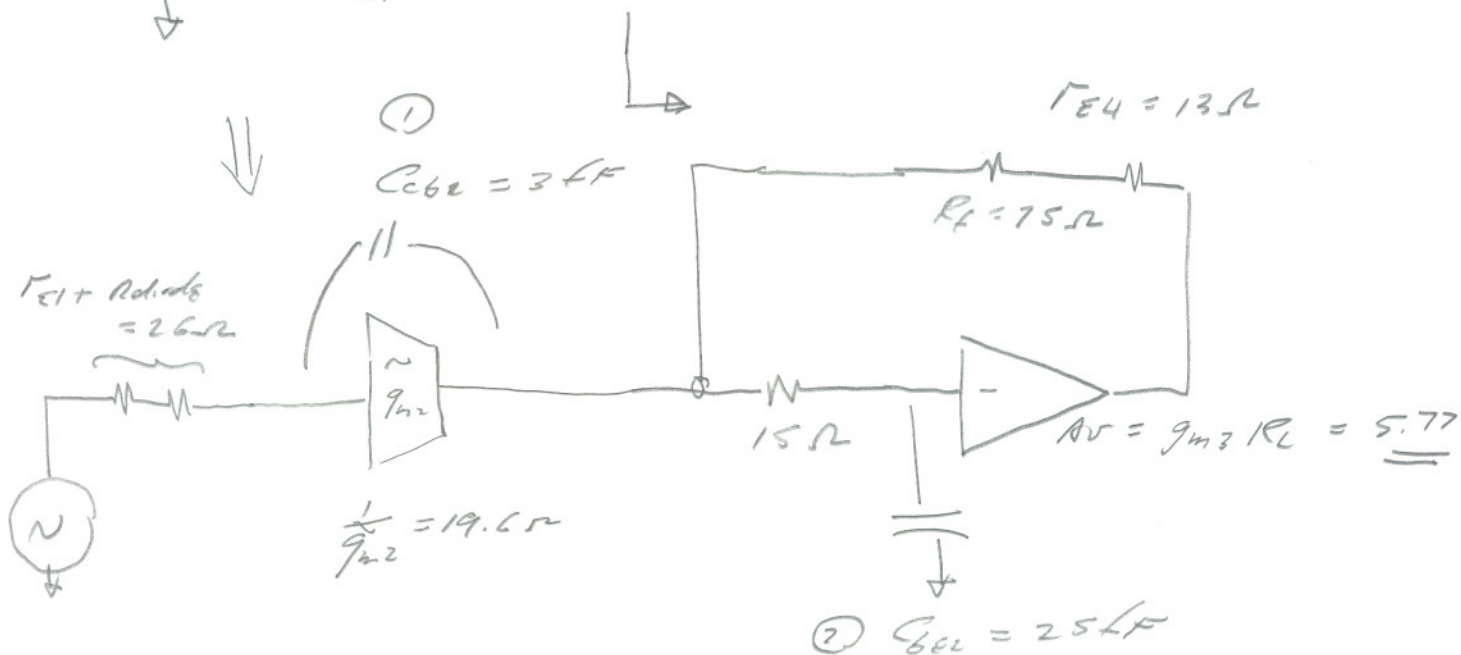
$$a_1 = 549 \text{ fs}$$

$$a_2 = 7 \cdot 10^{-26} \text{ sec}^2$$

and from this estimate the circuit bandwidth (and--if relevant---damping factor.)

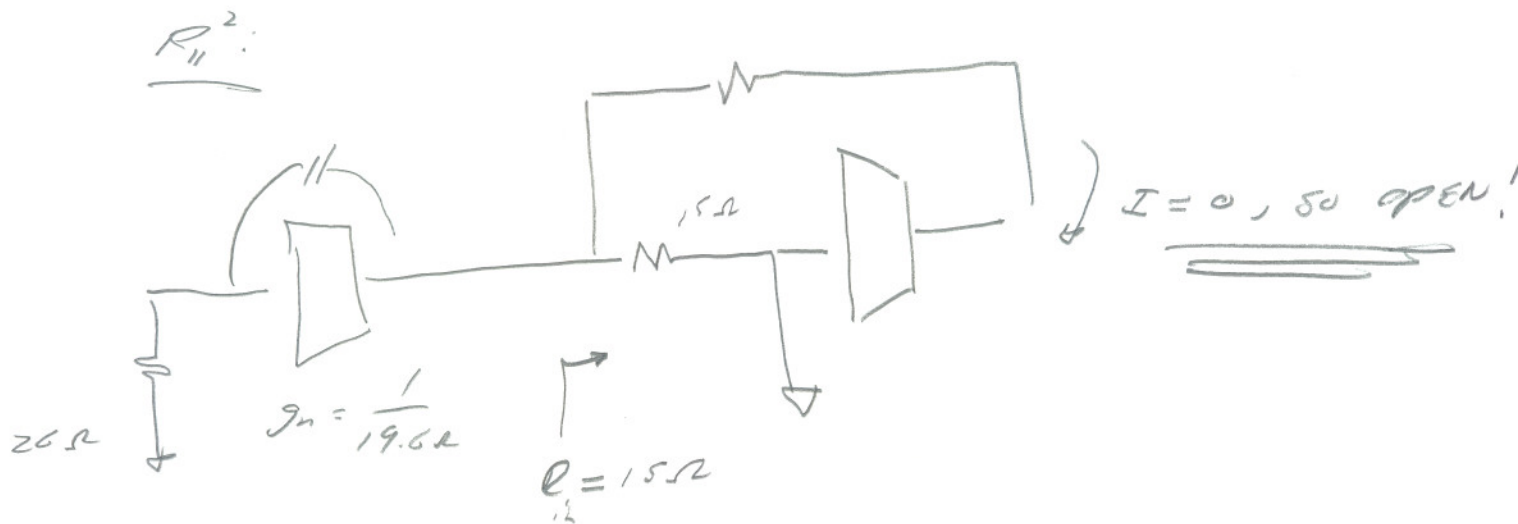


$$R_{i2} = \frac{75 + 13 \Omega}{6.77} = 12.99 \Omega$$



$$R_{i1}^0 = 26 \left(1 + \frac{12.99}{19.6} \right) + 12.99 \Omega = 56.2 \Omega$$

$$R_{i2}^0 = \frac{15 \Omega + 75 \Omega + 13 \Omega}{6.77} = 15.2 \Omega$$



$$R_{11}^2 = 26 \Omega \left(1 + \frac{15 \Omega}{19.6 \Omega} \right) + 15 \Omega = 60.9 \Omega$$

$$\begin{aligned} \tau_1 &= R_{11}^0 C_1 + R_{22}^0 C_2 = 56.2 \Omega \cdot 3 \text{ fF} + 15.2 \Omega \cdot 25 \text{ fF} \\ &= 169 \text{ fS} + 380 \text{ fS} = \underline{\underline{549 \text{ fS}}} \end{aligned}$$

$$\begin{aligned} \tau_2 &= R_{11}^2 C_1 C_2 R_{22}^0 = 60.9 \Omega \cdot 3 \text{ fF} \cdot 380 \text{ fS} = \\ &= \underline{\underline{6.94 \cdot 10^{-26} \text{ sec}^2}} \end{aligned}$$